High Current Transistors

PNP Silicon

Features

• This is a Pb–Free Device*



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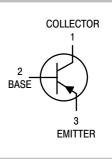


Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-80	Vdc
Collector – Base Voltage	V _{CBO}	-80	Vdc
Emitter – Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current – Continuous	Ι _C	-1.0	Adc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	PD	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

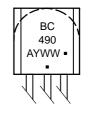
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.





MARKING DIAGRAM



A = Assembly Location Y = Year WW = Work Week • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BC490G	TO–92 (Pb–Free)	5000 Units / Bulk

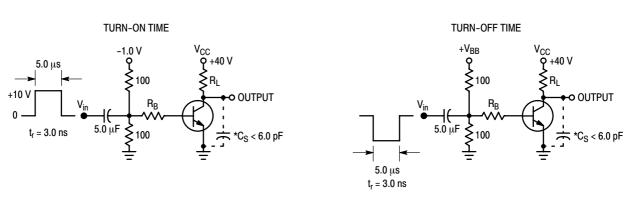
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BC490

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

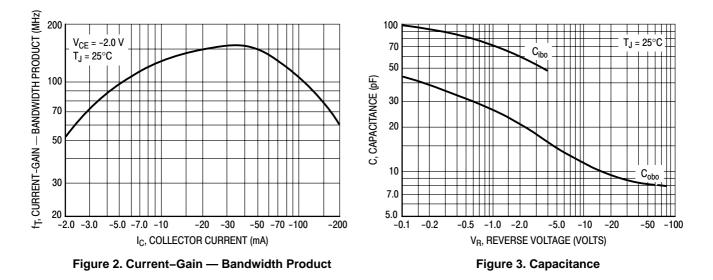
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Collector – Emitter Breakdown Voltage (Note 1) $(I_{C} = -10 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	-80	-	_	Vdc
Collector-Base Breakdown Voltage $(I_{C} = -100 \ \mu Adc, I_{E} = 0)$	V _{(BR)CBO}	-80	-	_	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-4.0	-	_	Vdc
Collector Cutoff Current ($V_{CB} = -60 \text{ Vdc}, I_E = 0$)	I _{CBO}	_	-	-100	nAdc
ON CHARACTERISTICS	ŀ				
DC Current Gain $(I_C = -10 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc})$ $(I_C = -100 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc})$ $(I_C = -1.0 \text{ Adc}, V_{CE} = -5.0 \text{ Vdc})$	h _{FE}	40 60 15	- - -	- 400 -	-
Collector – Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$) ($I_C = -1.0 \text{ Adc}$, $I_B = -100 \text{ mAdc}$)	V _{CE(sat)}		-0.25 -0.5	-0.5 -	Vdc
Base – Emitter Saturation Voltage $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$ $(I_C = -1.0 \text{ Adc}, I_B = -100 \text{ mAdc})$	V _{BE(sat)}		-0.9 -1.0	-1.2 -	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = -50$ mAdc, $V_{CE} = -2.0$ Vdc, f = 100 MHz)	f _T	-	150	-	MHz
Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{ob}	_	9.0	_	pF
Input Capacitance $(V_{EB} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C _{ib}	-	110	-	pF

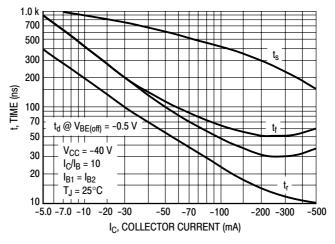
1. Pulse Test: Pulse Width = 300 μs, Duty Cycle 2%.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities









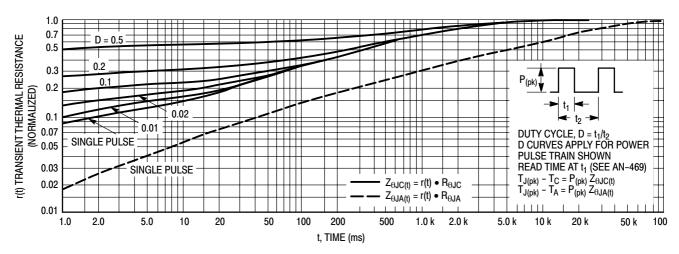


Figure 5. Thermal Response

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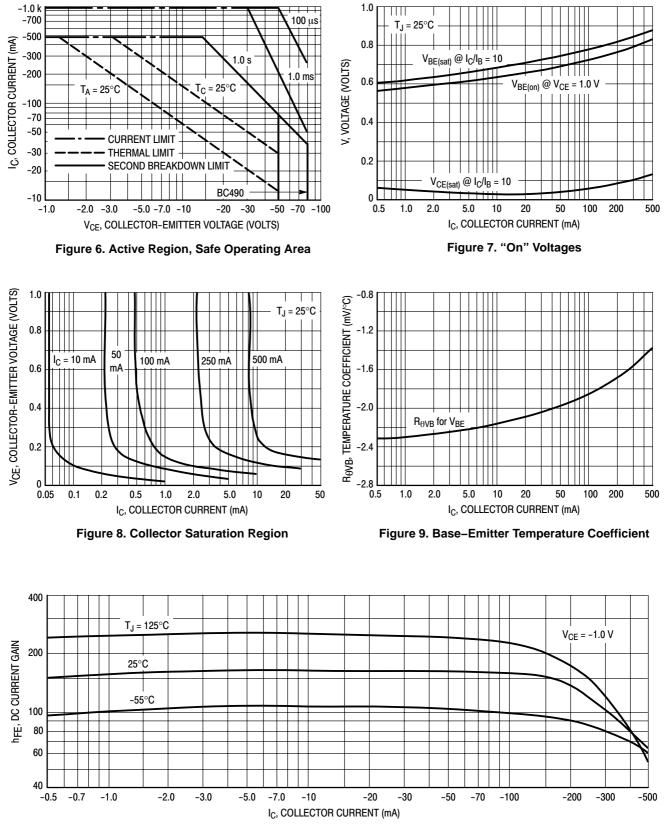


Figure 10. DC Current Gain

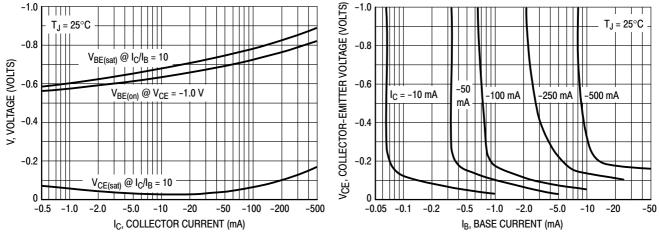


Figure 11. "On" Voltages

Figure 12. Collector Saturation Region

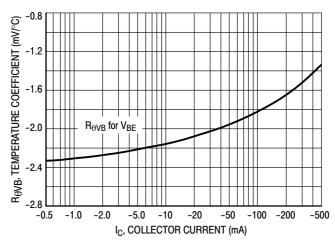
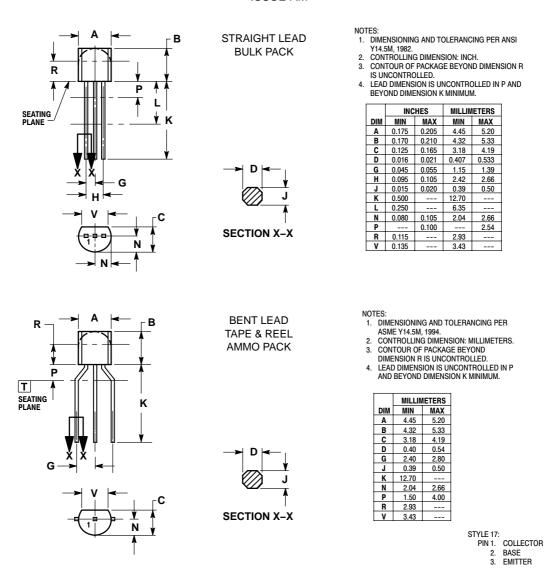


Figure 13. Base–Emitter Temperature Coefficient

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PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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